

NIF5003NT3G-VB Datasheet

N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

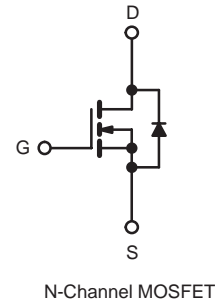
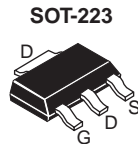
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
60	0.028 at $V_{GS} = 10$ V	7.0
	0.033 at $V_{GS} = 4.5$ V	5.6

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	60		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current ($T_J = 175\text{ }^{\circ}\text{C}$) ^a	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	7.0	6.0	A
	$T_A = 70\text{ }^{\circ}\text{C}$		6.1	5.0	
Pulsed Drain Current		I_{DM}	40		
Avalanche Current		I_{AS}	15		
Single Pulse Avalanche Energy		E_{AS}	11		mJ
Maximum Power Dissipation ^a	$T_A = 25\text{ }^{\circ}\text{C}$	P_D	3.3	1.7	W
	$T_A = 70\text{ }^{\circ}\text{C}$		2.3	1.2	
Operating Junction and Storage Temperature Range		T_J, T_{stq}	- 55 to 175		$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	36	45	°C/W
		75	90	
Maximum Junction-to-Foot (Drain)	R_{thJF}	17	20	

Notes:

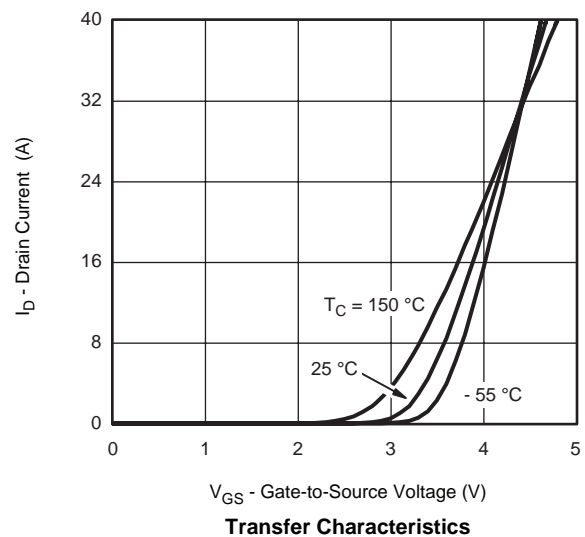
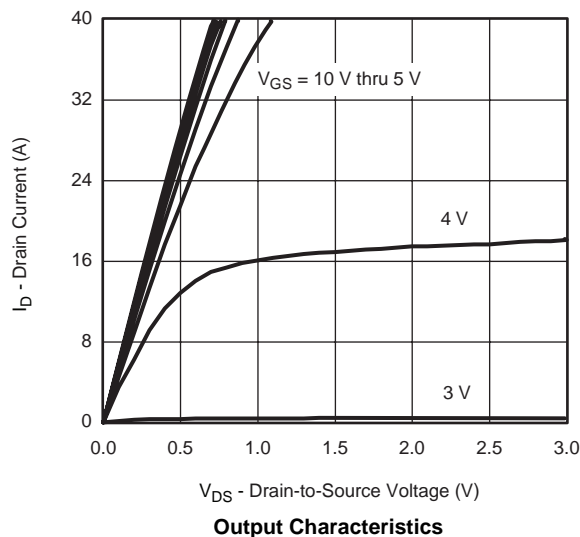
a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$			20	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 6.0\text{ A}$		0.028		Ω
		$V_{GS} = 10\text{ V}$, $I_D = 6.0\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		0.032		
		$V_{GS} = 10\text{ V}$, $I_D = 6.0\text{ A}$, $T_J = 175\text{ }^{\circ}\text{C}$		0.040		
		$V_{GS} = 4.5\text{ V}$, $I_D = 5.1\text{ A}$		0.033		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 6.0\text{ A}$		25		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1.7\text{ A}$, $V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 6.0\text{ A}$		18	27	nC
Gate-Source Charge	Q_{gs}			3.4		
Gate-Drain Charge	Q_{gd}			5.3		
Gate Resistance	R_g	$V_{GS} = 0.1\text{ V}$, $f = 5\text{ MHz}$	0.5	1.4	2.4	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}$, $R_L = 30\text{ }\Omega$ $I_D \cong 1\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 6\text{ }\Omega$		10	20	ns
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			25	50	
Fall Time	t_f			12	24	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		50	80	

Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$, unless otherwise noted

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

On-Resistance vs. Drain Current

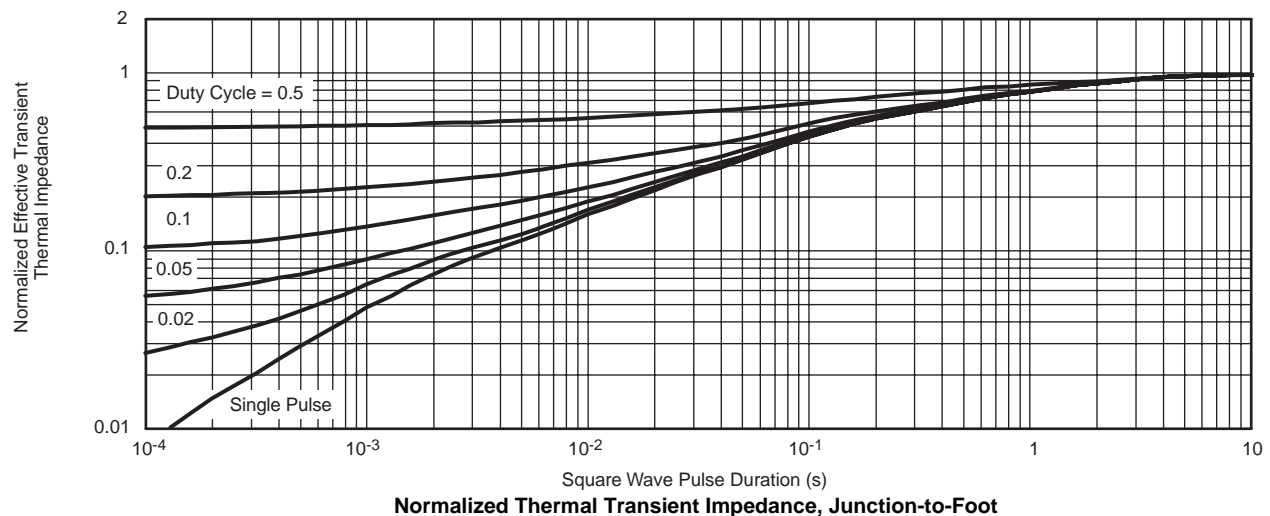
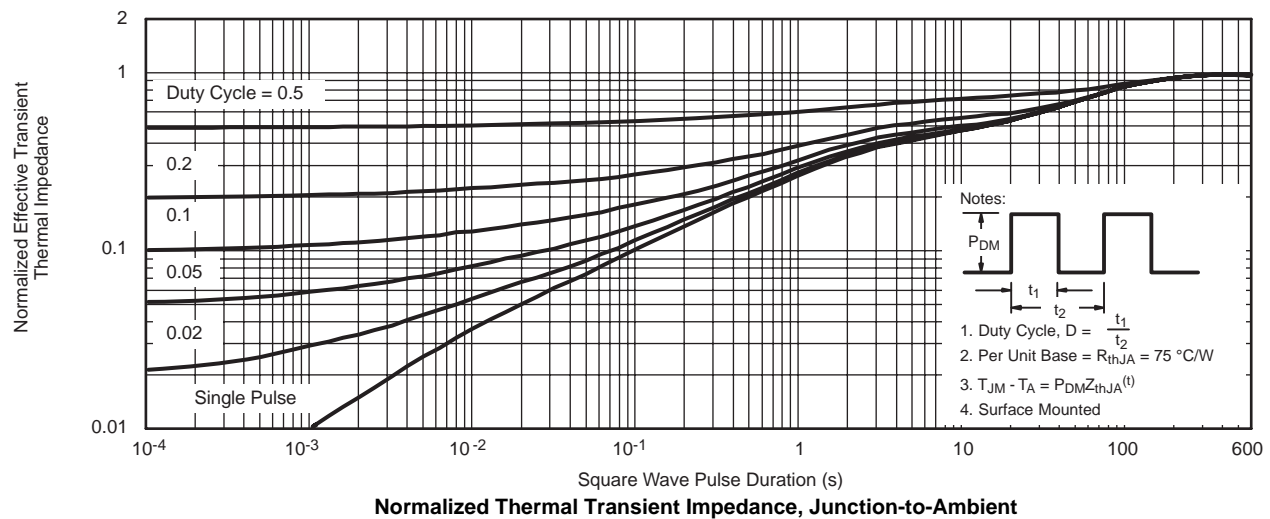
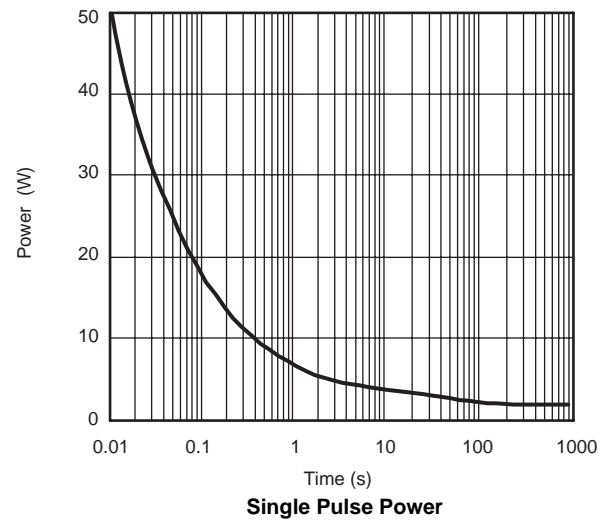
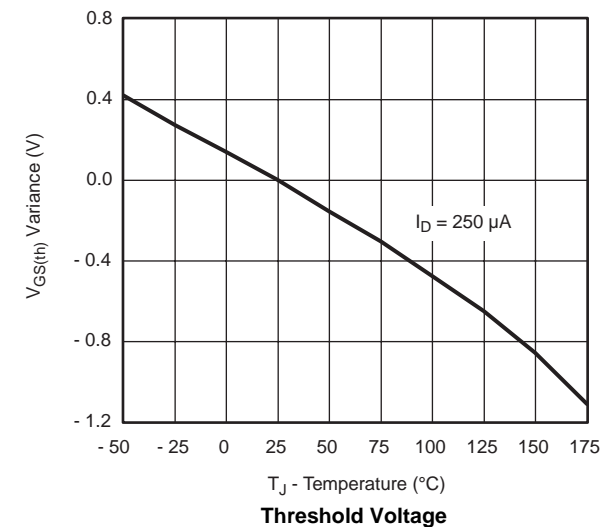
Capacitance

Gate Charge

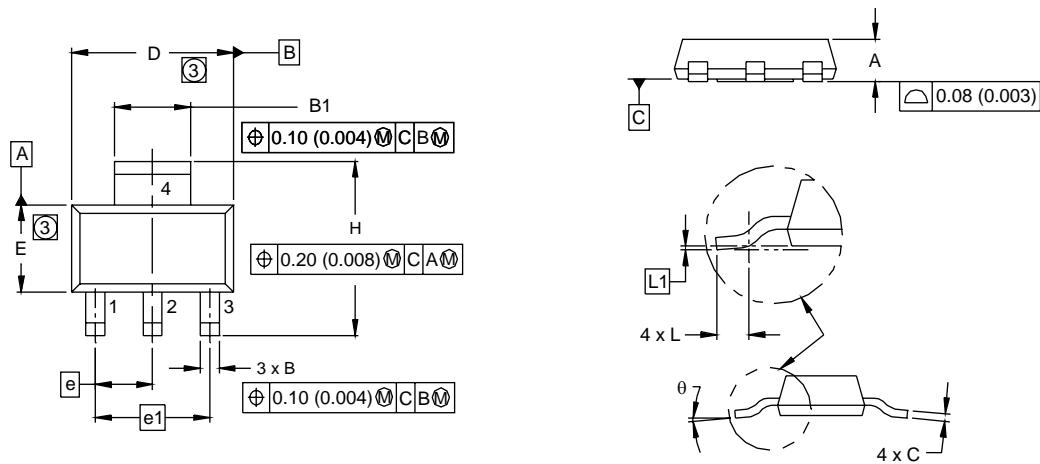
On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


SOT-223 (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	1.55	1.80	0.061	0.071
B	0.65	0.85	0.026	0.033
B1	2.95	3.15	0.116	0.124
C	0.25	0.35	0.010	0.014
D	6.30	6.70	0.248	0.264
E	3.30	3.70	0.130	0.146
e	2.30 BSC		0.0905 BSC	
e1	4.60 BSC		0.181 BSC	
H	6.71	7.29	0.264	0.287
L	0.91	-	0.036	-
L1	0.061 BSC		0.0024 BSC	
θ	-	10°	-	10°
ECN: S-82109-Rev. A, 15-Sep-08 DWG: 5969				

- Notes**
1. Dimensioning and tolerancing per ASME Y14.5M-1994.
 2. Dimensions are shown in millimeters (inches).
 3. Dimension do not include mold flash.
 4. Outline conforms to JEDEC outline TO-261AA.

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